

Silicon NPN Power Transistors

2SC4508

DESCRIPTION

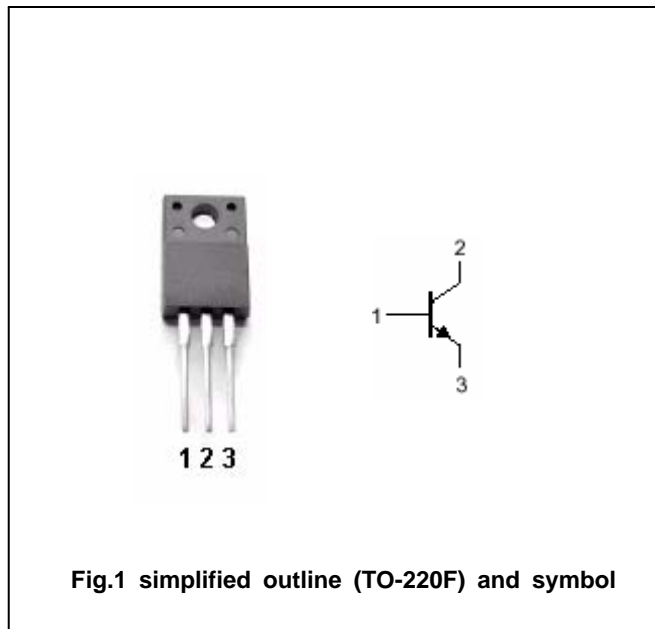
- With TO-220F package
- High breakdown voltage
- High speed switching performance

APPLICATIONS

- For switching regulator and general purpose power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
P_C	Collector dissipation	$T_C=25$	40	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustainig voltage	I _C =100mA ; I _B =0	400			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	500			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A ; I _B =0.8A			0.8	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A ; I _B =0.8A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =450V; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			100	μ A
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	25		65	
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =5V	20			

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PACKAGE OUTLINE

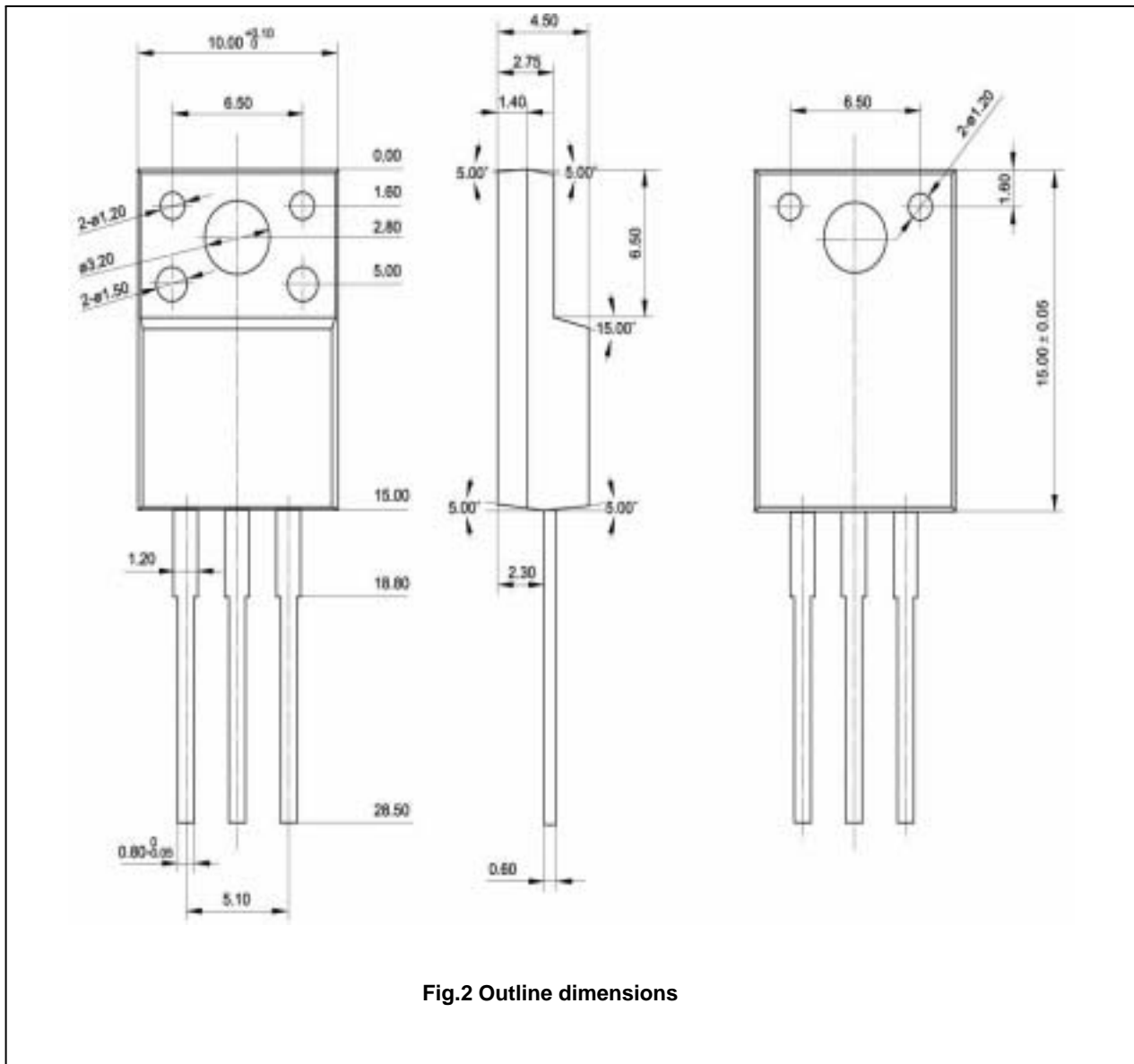


Fig.2 Outline dimensions